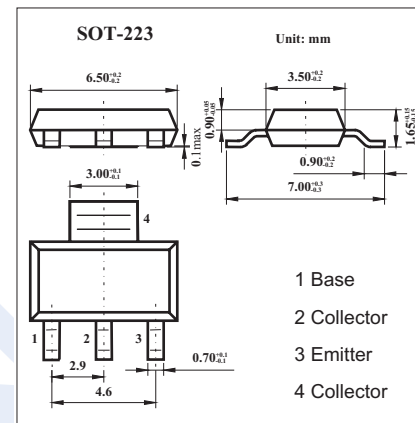


2.0W Surface Mount Complementary PNP Silicon Power Transistor KZT2955 (CZT2955)

■ Features

- High current (max. 6A).
- Low voltage (max. 60V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-100	V
Collector - emitter voltage	V _{CER}	-70	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EBO}	-7	V
Collector current	I _C	-6	A
Base current	I _B	-3	A
Power dissipation	P _D	2	W
Thermal resistance, Junction-to-ambient	R _{θJA}	62.5	°C/W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector to emitter breakdown voltage	V _{CEO}	I _C = -30mA	-60			V
Collector to emitter breakdown voltage	V _{CER}	I _C = -30mA, R _{BE} = 100 Ω	-70			V
Collector cutoff current	I _{CEO}	V _{CE} = -30V			-700	μA
	I _{CEV}	V _{CE} = -100V, V _{EB} = -1.5V			1.0	mA
Emitter cutoff current	I _{EBO}	V _{EB} = -7.0 V			-5.0	mA
DC current gain	h _{FE}	I _C = -4.0A; V _{CE} = -4.0 V	20		70	
		I _C = -6.0A; V _{CE} = -4.0V	5.0			
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -4.0A; I _B = -400mA			-1.1	V
Base to emitter ON voltage	V _{BE(on)}	V _{CE} = -4.0V, I _C = -4.0A			-1.5	V
Transition frequency	f _T	I _C = -500mA; V _{CE} = -10V; f = 1.0 MHz	2.5			MHz